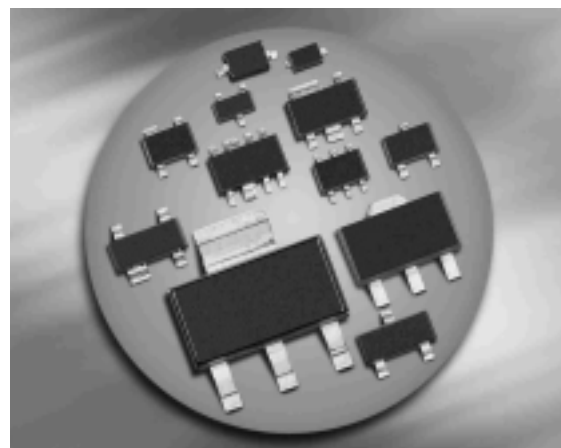


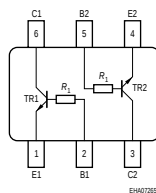
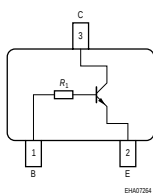
NPN silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in resistor ($R_1=4.7\text{ k}\Omega$)
- BCR119S: Two internally isolated transistors with good matching in one multichip package
- BCR119S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



BCR119/F/W

BCR119S



Type	Marking	Pin Configuration						Package
BCR119	WKs	1=B	2=E	3=C	-	-	-	SOT23
BCR119F	WKs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR119S	WKs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR119W	WKs	1=B	2=E	3=C	-	-	-	SOT323

¹⁾Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	30	
Input reverse voltage	$V_{i(rev)}$	5	
DC collector current	I_E	100	mA
Total power dissipation- BCR119, $T_S \leq 102^\circ\text{C}$ BCR119F, $T_S \leq 128^\circ\text{C}$ BCR119S, $T_S \leq 115^\circ\text{C}$ BCR119W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BCR119 BCR119F BCR119S BCR119W	R_{thJS}	≤ 240 ≤ 90 ≤ 140 ≤ 105	K/W

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{\text{CB}} = 40\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{\text{EB}} = 5\ \text{V}$, $I_C = 0$	I_{EBO}	-	-	100	nA
DC current gain ¹⁾ $I_C = 5\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	120	-	630	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.4	-	0.8	
Input on voltage $I_C = 2\ \text{mA}$, $V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	0.5	-	1.1	
Input resistor	R_1	3.2	4.7	6.2	kΩ

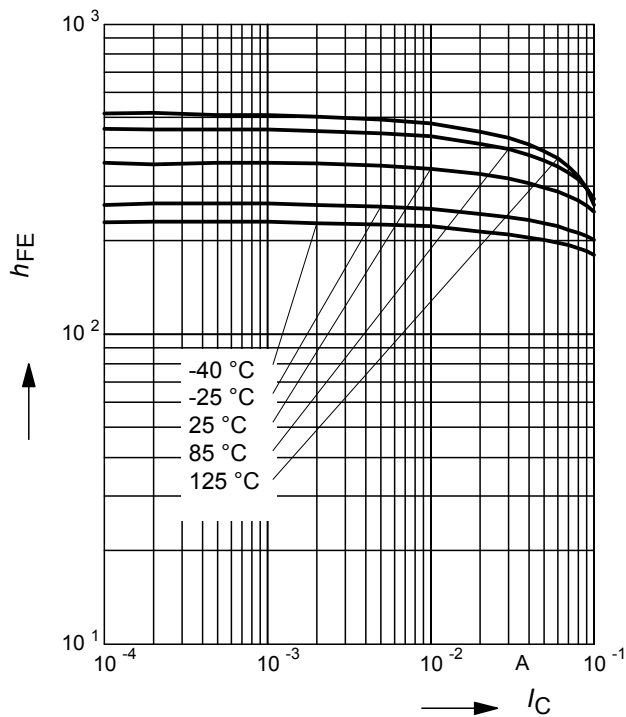
AC Characteristics

Transition frequency $I_C = 10\ \text{mA}$, $V_{CE} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

¹Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

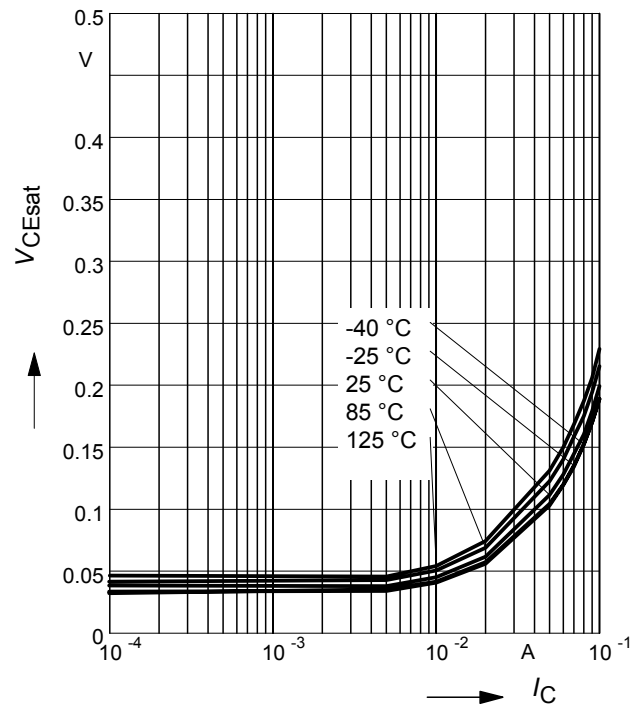
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



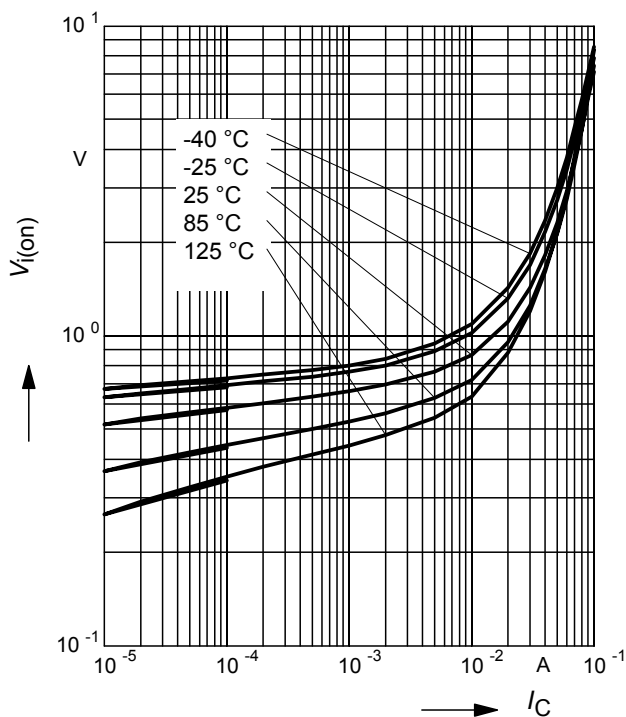
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, $I_C/I_B = 20$



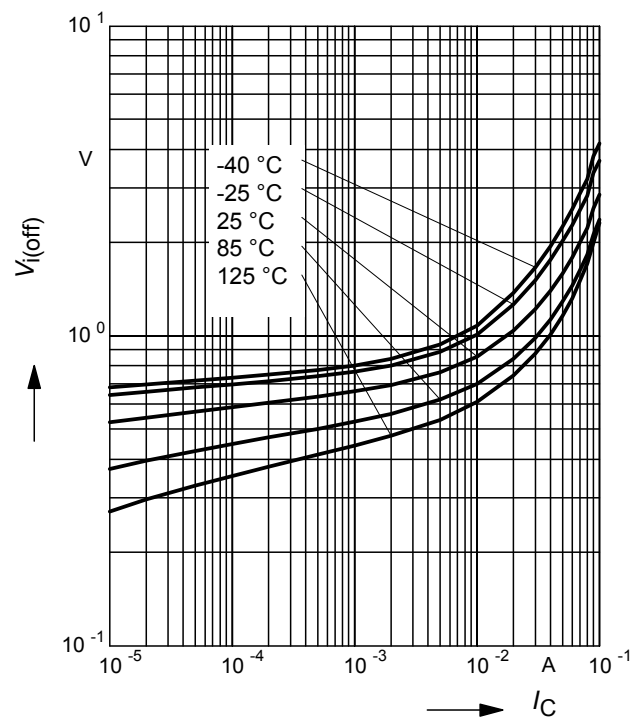
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)



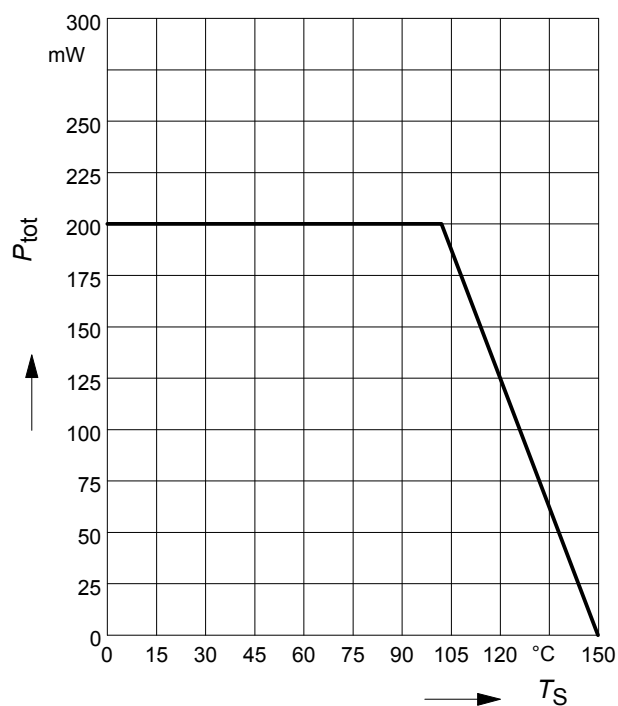
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



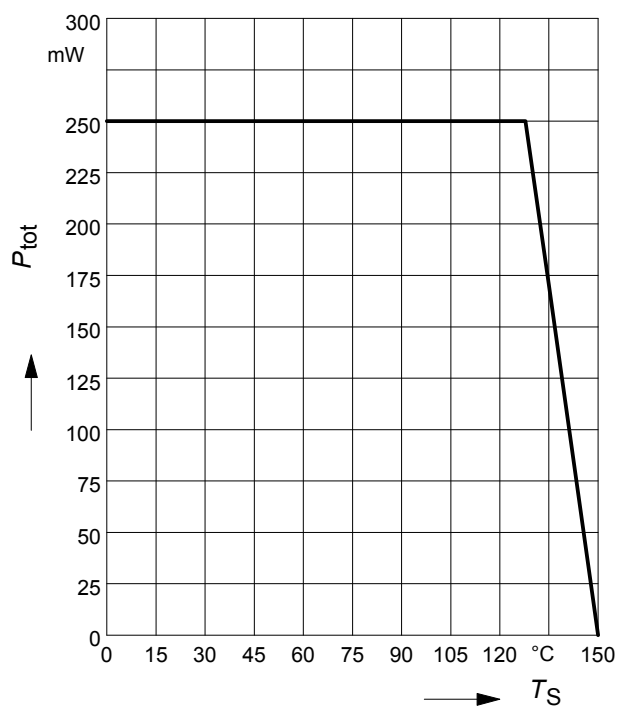
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR119



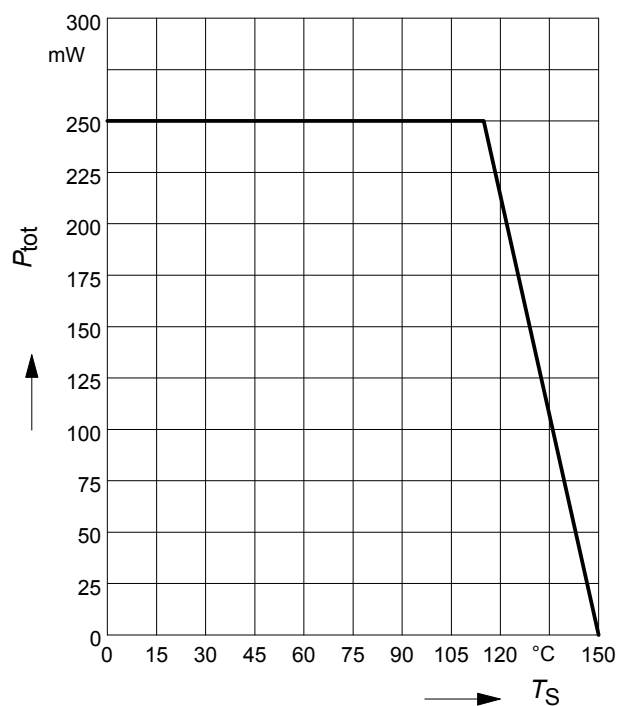
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR119F



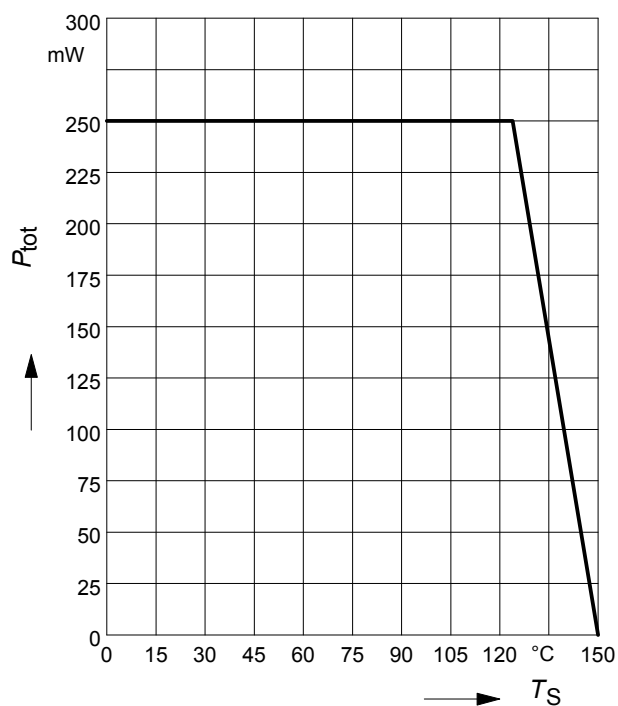
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR119S



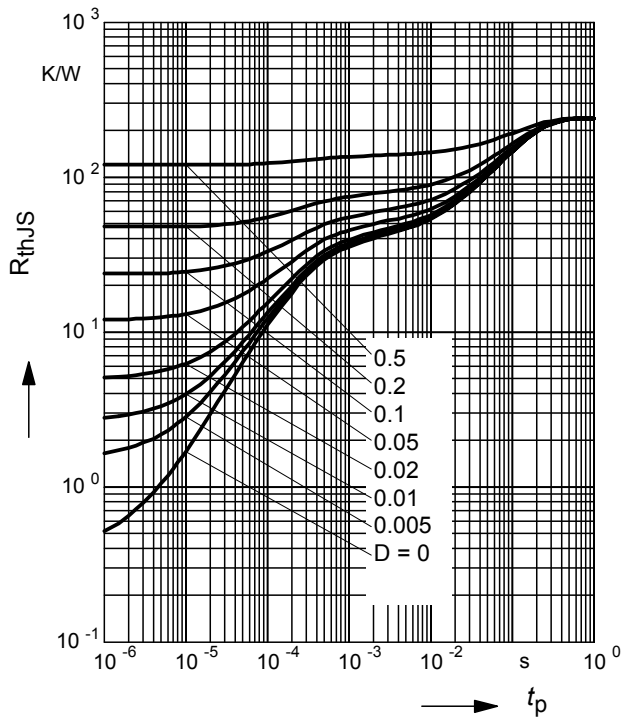
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR119W



Permissible Pulse Load $R_{thJS} = f(t_p)$

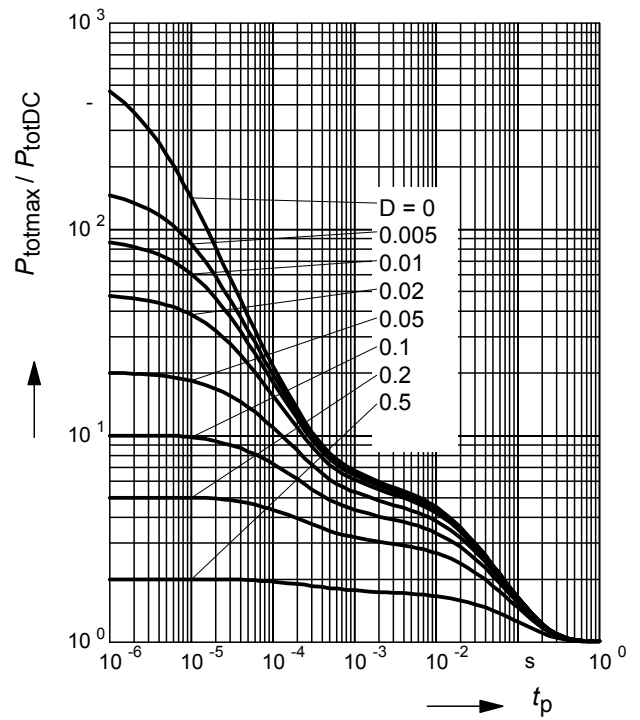
BCR119



Permissible Pulse Load

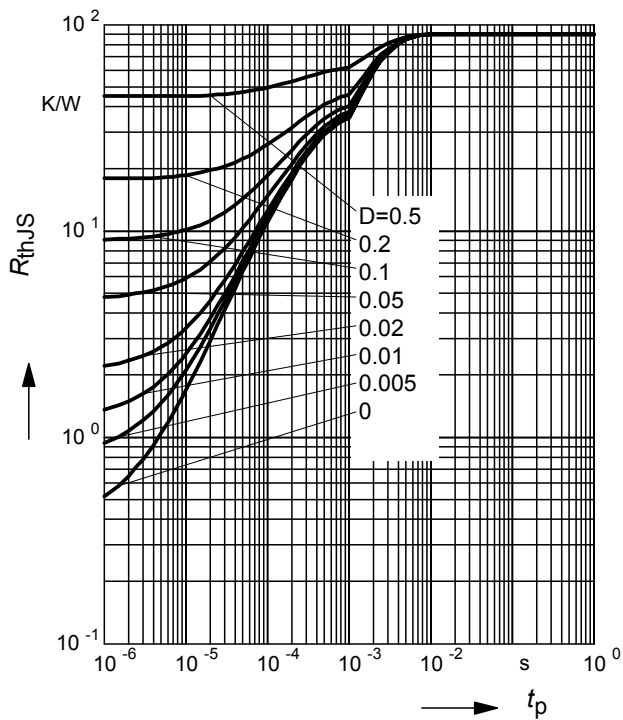
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR119



Permissible Puls Load $R_{thJS} = f(t_p)$

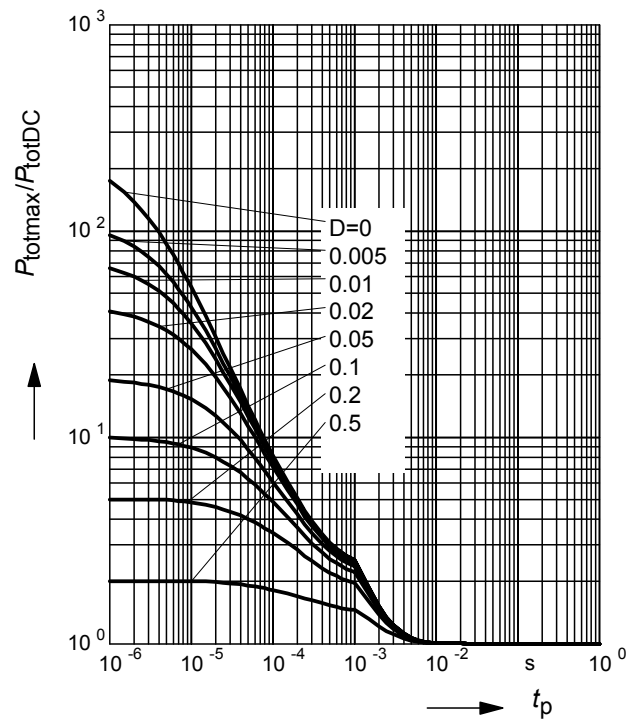
BCR119F



Permissible Pulse Load

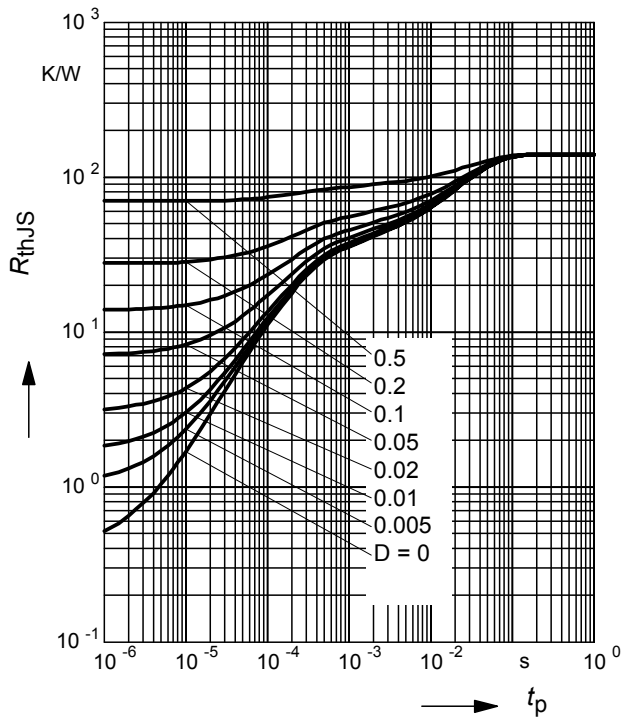
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR119F



Permissible Puls Load $R_{thJS} = f(t_p)$

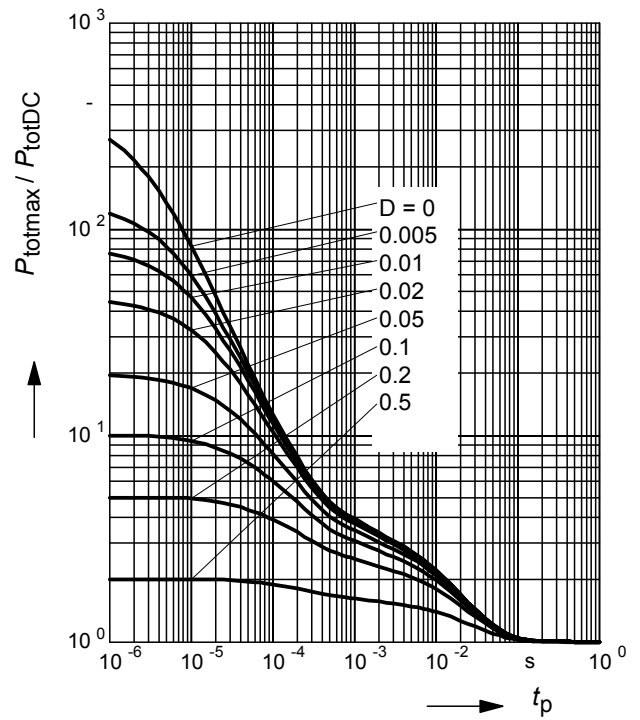
BCR119S



Permissible Pulse Load

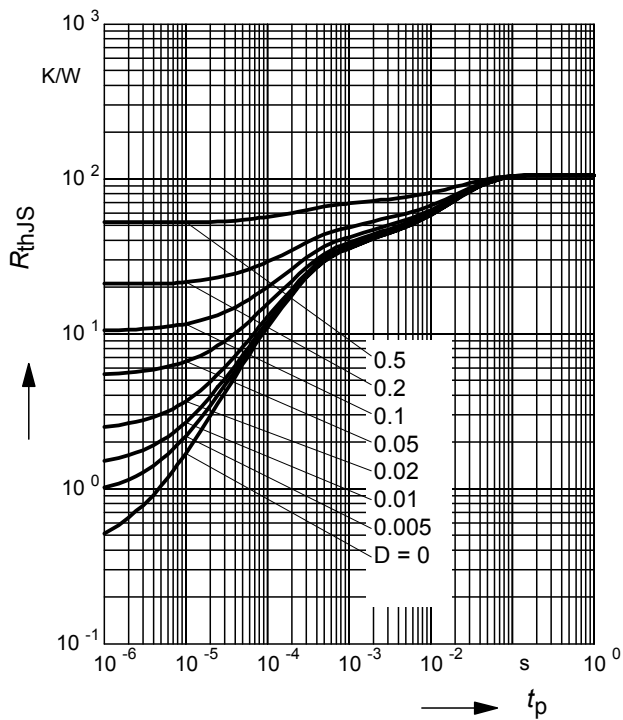
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR119S



Permissible Puls Load $R_{thJS} = f(t_p)$

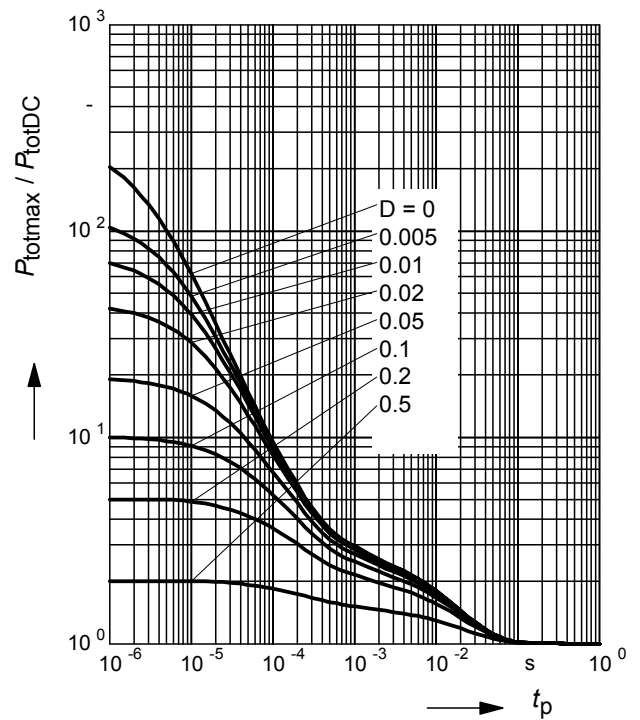
BCR119W



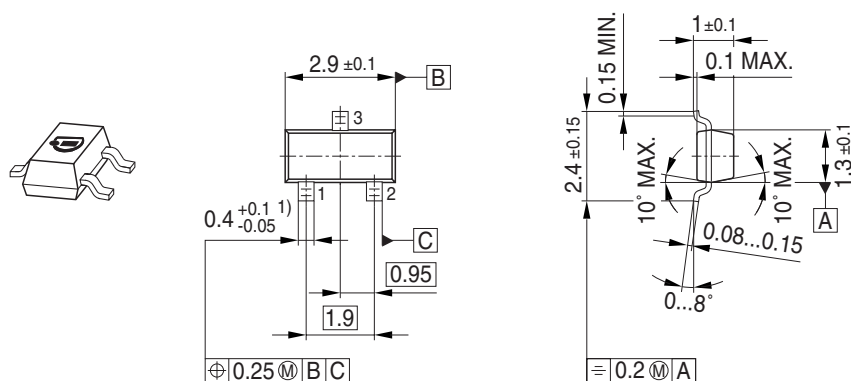
Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR119W

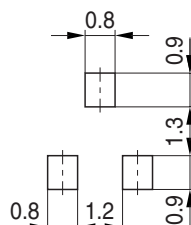


Package Outline

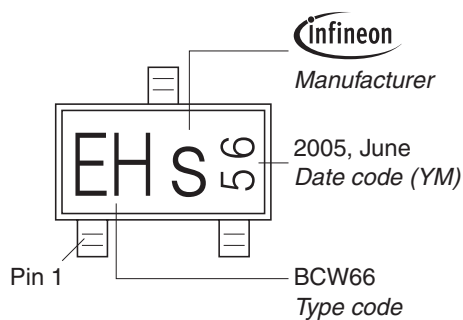


1) Lead width can be 0.6 max. in dambar area

Foot Print

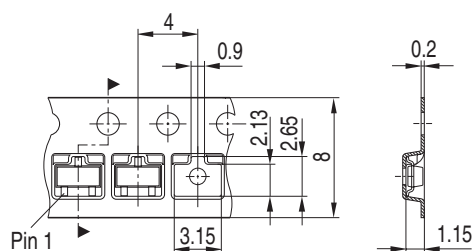


Marking Layout (Example)

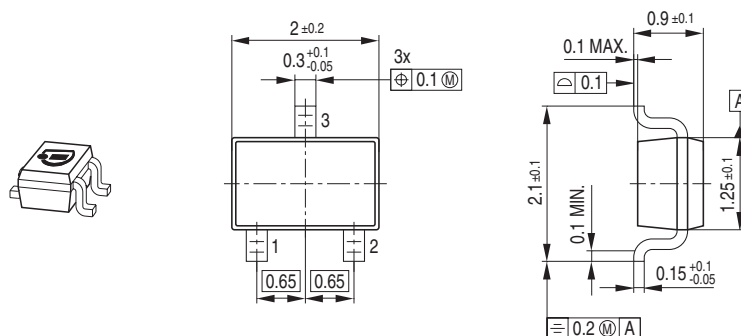


Standard Packing

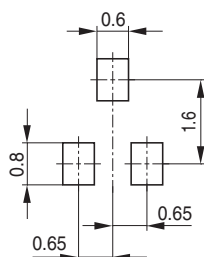
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



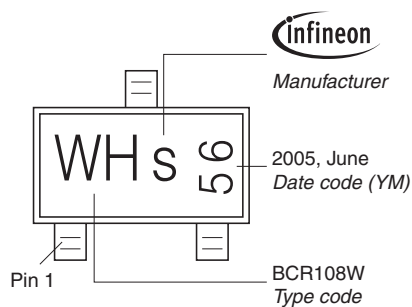
Package Outline



Foot Print

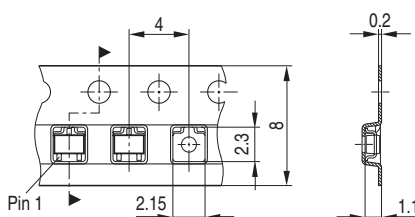


Marking Layout (Example)

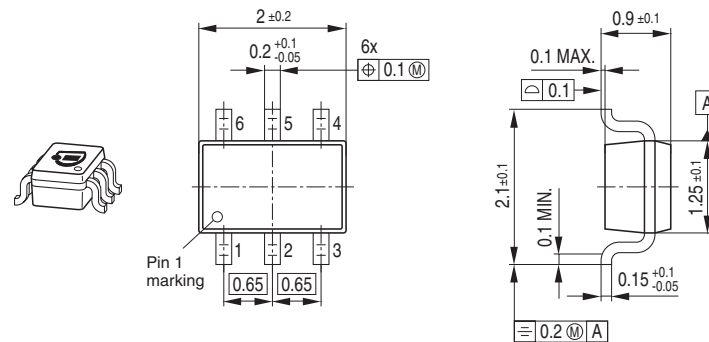


Standard Packing

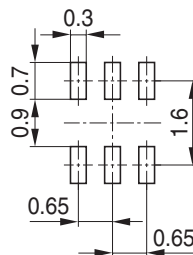
Reel $\varnothing 180 \text{ mm}$ = 3.000 Pieces/Reel
 Reel $\varnothing 330 \text{ mm}$ = 10.000 Pieces/Reel



Package Outline

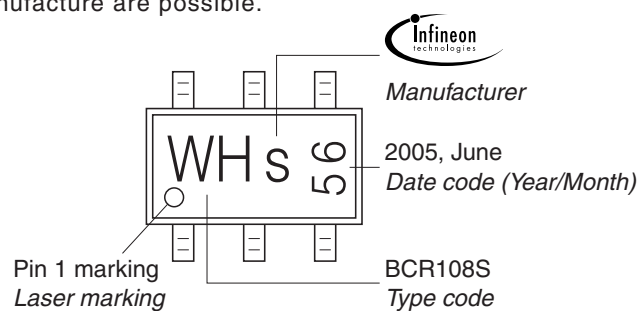


Foot Print



Marking Layout (Example)

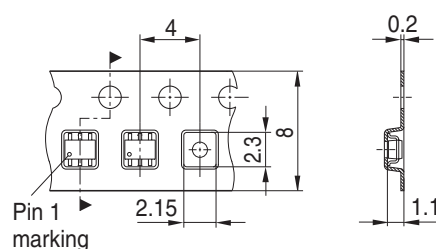
Small variations in positioning of
Date code, Type code and Manufacture are possible.



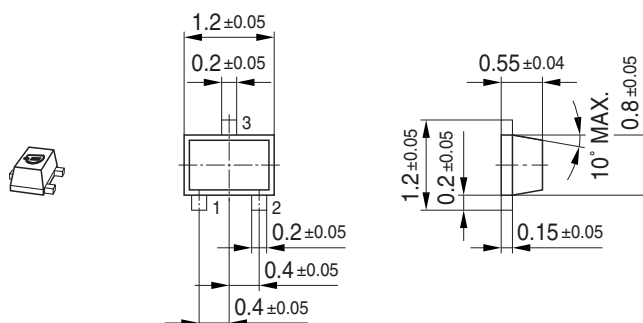
Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

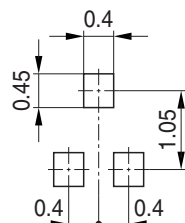
For symmetric types no defined Pin 1 orientation in reel.



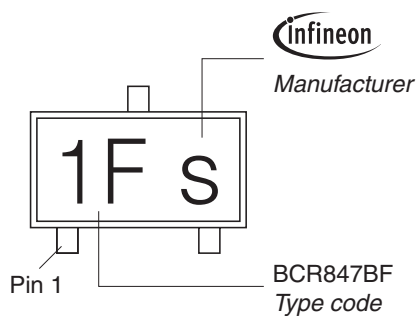
Package Outline



Foot Print

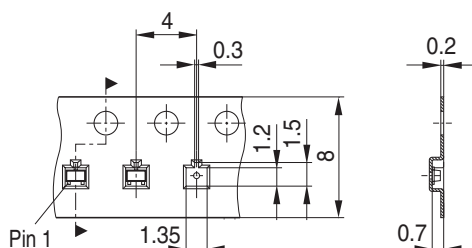


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



Edition 2006-02-01

Published by

Infineon Technologies AG

81726 München, Germany

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Наши контакты:

Телефон: +7 812 627 14 35

Электронная почта: sales@st-electron.ru

Адрес: 198099, Санкт-Петербург,
Промышленная ул, дом № 19, литера Н,
помещение 100-Н Офис 331